

Crystallographers

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This section is intended to be a series of short paragraphs dealing with the activities of crystallographers, such as their changes of position, promotions, assumption of significant new duties, honours, etc. Items for inclusion, subject to the approval of the Editorial Board, should be sent to the Executive Secretary of the International Union of Crystallography (J. N. King, International Union of Crystallography, 5 Abbey Square, Chester CH1 2HU, England).

Heinz Bilz, one of the directors of the Max-Planck-Institut für Festkörperforschung, died unexpectedly on 26 June 1986, shortly after his 60th birthday.

Heinz Bilz was born in Berlin on 18 May 1926. After the war he began to study physics at the University of Frankfurt am Main. In 1958 he obtained his PhD in physics under F. Hund with a dissertation entitled 'Electronic States of Refractory Compounds'. In 1964 he became full Professor for Theoretical Physics in Frankfurt. Five years later he moved to the Technical University of Munich. Finally, in 1972 he became Director at the newly established Max-Planck Institut für Solid-State Research in Stuttgart. Dr A. Rabenau writes that Professor Bilz's main field of interest was the theory of lattice dynamics to which he contributed more than 100 scientific papers and two books. In recent years he was concerned in particular with electron-phonon coupling, soft modes, structural phase transitions and the relations between structure and dynamics. Despite being a theorist, he was widely known for his ability to communicate effectively with experimentalists. The door of his office was always open to anybody who had a problem. Many of his colleagues and students will still remember stimulating and fruitful discussions with him. He had the ingenious ability to produce quickly stimulating ideas during such discussions. Apart from his scientific merits, one of his outstanding characteristics was that he enjoyed being a magnanimous host. His house was a frequent meeting place for colleagues, students, and the guests of the Institute. His interests ranged from physics and philosophy to classical music. He was an outstanding human being and a first class scientist. With his death we have lost a dear friend and colleague.

With deep distress the scientific community has learned about the unexpected death of Professor **Werner Schmatz** by a heart attack, on 13 November 1986. Born in 1933 in Munich, he studied physics at the Munich University and, after several years in the Physikalisch Technische Bundesanstalt in Braunschweig, he finished his thesis in 1960; he then started to work at the Munich research reactor under Professor H. Maier-Leibnitz. In 1964 he went to the KFA Jülich, where,

in 1973, he became one of the Directors at the Institut für Festkörperforschung; simultaneously, he was appointed Professor at the University of Bochum. Professor Dr T. Springer writes that during this time in Jülich, his primary research efforts were focused on the study of disordered metals by means of neutron scattering techniques. His research efforts, and those of his co-workers, were internationally recognized; consider for example, the investigations on radiation damage and precipitates by neutron small-angle scattering, or the diffuse scattering studies of lattice displacements around impurities. He also introduced the H₂O/D₂O contrast method in small-angle scattering investigations of biological molecules, for example hemoglobin. It was a period of pioneer work. His main interest turned to physical problems, but he also considered the promotion and improvement of scientific methods as the key to scientific progress. In 1977, he left the KFA Jülich to become Director of the Institute for Applied Nuclear Physics in the KfK Karlsruhe where he also started work on high-resolution electron-energy-loss spectroscopy. The friends and colleagues of Werner Schmatz will always remember his enthusiasm and open-mindedness, and his untiring commitment to his co-workers and students.

Professor **N. N. Greenwood**, Department of Inorganic and Structural Chemistry, Leeds University, has been elected a Fellow of the Royal Society for wide-ranging synthetic and structural studies on compounds of boron.

Dr **Olga Kennard**, Director of the Cambridge Crystallographic Data Centre, has been elected a Fellow of the Royal Society in recognition of her investigations of organic molecules by diffraction methods.

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